2SD2413

Silicon NPN triple diffusion planar type

For low-frequency output amplification

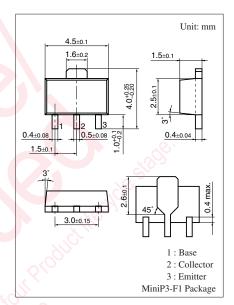
■ Features

- High collector-base voltage (Emitter open) V_{CBO}
- ullet High collector-emitter voltage (Base open) V_{CEO}
- Large collector power dissipation P_C
- Low collector-emitter saturation voltage V_{CE(sat)}
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	400	V	
Collector-emitter voltage (Base open)	V _{CEO}	400	V	
Emitter-base voltage (Collector open)	V_{EBO}	5	V	
Collector current	I _C	100	mA	
Peak collector current	I_{CP}	200	mA	
Collector power dissipation *	P _C	1	w	
Junction temperature	T_{j}	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

Note) *: Printed circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion



Marking Symbol: 1S

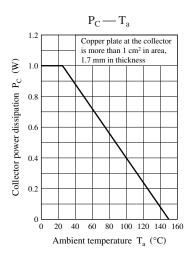
■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

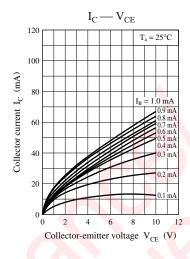
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = 100 \mu\text{A}, I_E = 0$	400			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 500 \mu\text{A}, I_B = 0$	400			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_E = 100 \mu\text{A}, I_C = 0$	5			V
Forward current transfer ratio	h _{FE}	$V_{CE} = 5 \text{ V}, I_{C} = 30 \text{ mA}$	30			_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$			1.5	V
Base-emitter saturation voltage	V _{BE(sat)}	$I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$			1.5	V
Transition frequency *	f_T	$V_{CB} = 30 \text{ V}, I_E = -20 \text{ mA}, f = 200 \text{ MHz}$		40		MHz
Collector output capacitance	C _{ob}	$V_{CB} = 30 \text{ V}, I_E = 0, f = 1 \text{ MHz}$			7	pF
(Common base, input open circuited)						

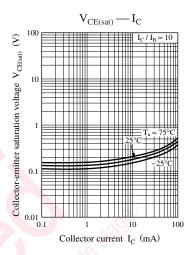
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

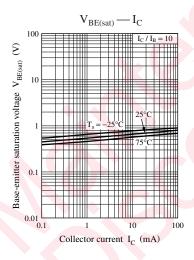
2. *: Pulse measurement

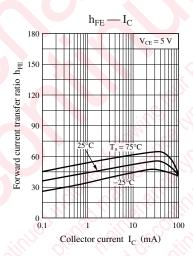
Panasonic

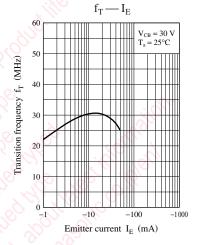


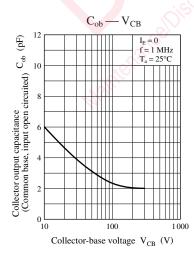












2 SJC00260BED

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